

PN2369_D26Z Datasheet



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DiGi Electronics Part Number PN2369_D26Z-DG

Manufacturer onsemi

Manufacturer Product Number PN2369_D26Z

Description TRANS NPN 15V 0.2A TO92-3

Detailed Description Bipolar (BJT) Transistor NPN 15 V 200 mA 350 mW T

hrough Hole TO-92-3



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PN236

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
PN2369_D26Z	onsemi
Series:	Product Status:
	Obsolete
Transistor Type:	Current - Collector (Ic) (Max):
NPN	200 mA
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
15 V	250mV @ 1mA, 10mA
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
400nA (ICBO)	40 @ 10mA, 1V
Power - Max:	Frequency - Transition:
350 mW	
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Through Hole
Package / Case:	Supplier Device Package:
TO-226-3, TO-92-3 (TO-226AA) Formed Leads	TO-92-3
Base Product Number:	

Environmental & Export classification

Moisture Sensitivity Level (MSL):	REACH Status:
1 (Unlimited)	REACH Unaffected
ECCN:	HTSUS:
FAR99	8541 21 0095



PN2369

NPN Switching Transistor

- This device is designed for high speed saturated switching at collector currents of 10mA to 100mA.
- Sourced from process 21.



Absolute Maximum Ratings* T_a =25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V _{CEO}	Collector-Emitter Voltage	15	V
V _{CBO}	Collector-Base Voltage	40	V
V _{EBO}	Emitter-Base Voltage	4.5	V
I _C	Collector Current - Continuous	200	mA
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 ~ 150	°C

^{*} This ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

These rating are based on a maximum junction temperature of 150 degrees C.
 These are steady limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

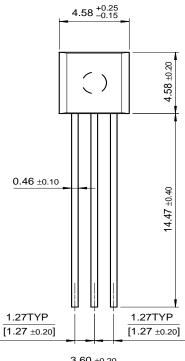
Electrical Characteristics T_a=25°C unless otherwise noted

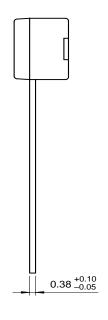
Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Charac	cteristics				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage *	$I_{C} = 10 \text{mA}, I_{B} = 0$	15		V
V _{(BR)CES}	Collector-Emitter Breakdown Voltage	$I_C = 10\mu A, V_{BE} = 0$	40		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 10\mu A, I_E = 0$	40		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 10\mu A, I_C = 0$	4.5		V
I _{CBO}	Collector Cutoff Current	$V_{CB} = 20V, I_{E} = 0$ $V_{CB} = 20V, I_{E} = 0, T_{a} = 125^{\circ}C$		0.4 30	μA μA
On Charac	cteristics				
h _{FE}	DC Current Gain *	$I_C = 10 \text{mA}, V_{CE} = 1.0 \text{V}$ $I_C = 100 \text{mA}, V_{CE} = 2.0 \text{V}$	40 20	120	
V _{CE(sat)}	Collector-Emitter Saturation Voltage *	I _C = 10mA, I _B = 1.0mA		0.25	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 10mA, I _B = 1.0mA	0.7	0.85	V
Small Sign	nal Characteristics				
C _{obo}	Output Capacitance	$V_{CB} = 5.0V, I_E = 0, f = 1.0MHz$ 4.0		4.0	pF
C _{ibo}	Input Capacitance	$V_{EB} = 0.5V, I_{C} = 0, f = 1.0MHz$		5.0	pF
h _{fe}	Small -Signal Current Gain	$I_C = 10 \text{mA}, V_{CE} = 10 \text{V}, R_G = 2.0 \text{k}\Omega,$ f = 100 MHz	5.0		
Switching	Characteristics			•	
t _s	Storage Time	$I_{B1} = I_{B2} = I_{C} = 10mA$		13	ns
t _{on}	Turn-On Time	$V_{CC} = 3.0V, I_{C} = 10mA, I_{B1} = 3.0mA$		12	ns
t _{off}	Turn-Off Time	$V_{CC} = 3.0V$, $I_{C} = 10$ mA, $I_{B1} = 3.0$ mA, $I_{B2} = 1.5$ mA		18	ns

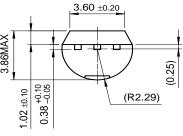
Thermal Characteristics T _a =25°C unless otherwise noted				
Symbol	Parameter	Max.	Units	
P _D	Total Device Dissipation Derate above 25°C	350 2.8	mW mW/°C	
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W	

Package Dimensions









Dimensions in Millimeters

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EnSigna™	ImpliedDisconnect™	OCXPro™	SILENT SWITCHER®	UltraFET [®]
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